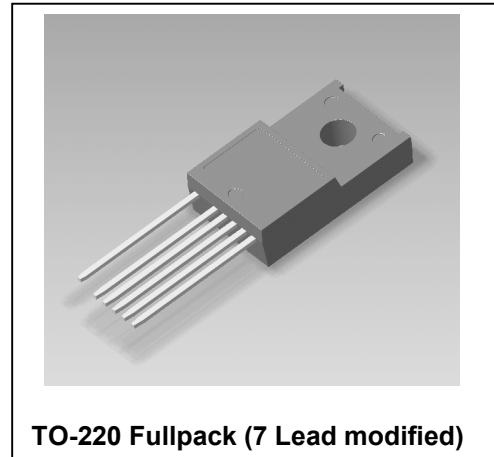


### INTEGRATED SWITCHER Package Outline



TO-220 Fullpack (7 Lead modified)

### Features

- 6-pin SIP type full molded package, optimum IC for low-height SMPS, with distance between high and low voltage pin 1.8 mm with pin elimination.
- Oscillator is provided on the monolithic control with adopting On-Chip Trimming Technology
- Small temperature characteristics variation by adopting a comparator to compensate for temperature on the control part.
- Low start-up circuit current (100uA max)
- Avalanche energy guaranteed MOSFET with high VDSS
  - The built-in power MOSFET simplifies the surge absorption circuit since the MOSFET guarantees the avalanche energy.
  - No VDSS de-rating is required.
- Built-in constant voltage drive circuit
- Built-in step drive circuit
- Built-in low frequency PWM mode ( 22 kHz)
- UVLO Burst Standby
- Two operational modes by auto switching functions according to load
  - For middle~heavy load operation : QR mode
  - For light~middle load operation : 1 Bottom Skip mode
- Various kinds of protection functions
  - Pulse-by-Pulse Overcurrent Protection (OCP)
  - Overvoltage Protection with Latch mode (OVP)
  - Overload Protection with Latch mode (OLP)
  - The maximum limit of on-time

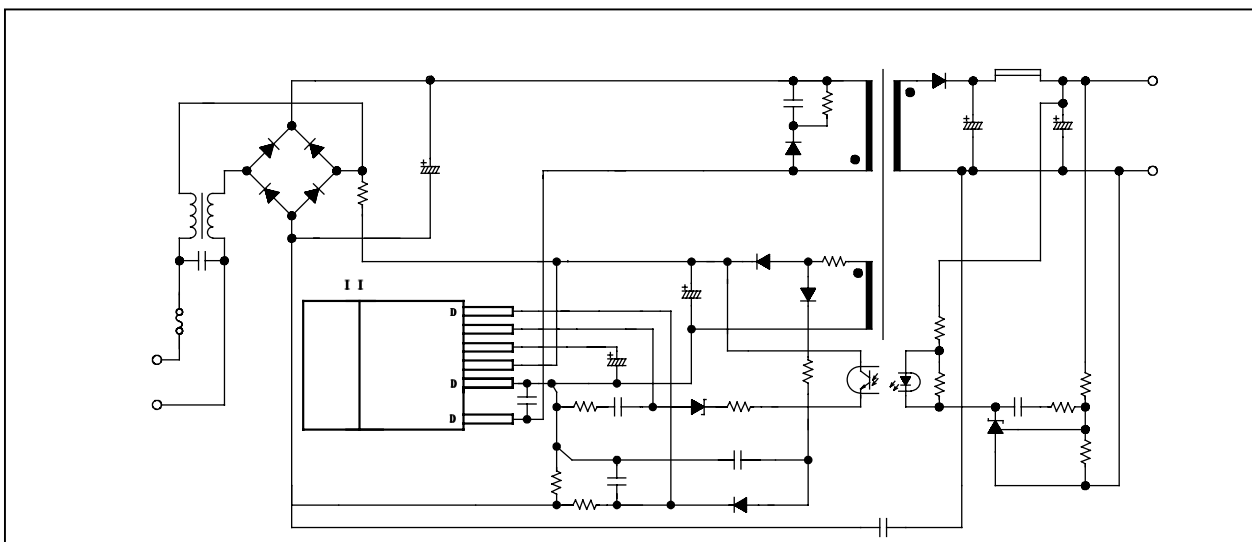
### Key Specifications

T type	MOSFET VDSS(V)	RDS(ON) MAX	AC input(V)		Pout(W) Note 1
			230	15%	120
IRIS-W6753	650		85 to 264		58

### Description

IRIS-W6753 is a hybrid IC consisting of a power MOSFET and a controller IC, designed for Quasi-Resonant (including low frequency PWM) fly-back converter type SMPS (Switching Mode Power Supply) applications. This IC realizes high efficiency, low noise, downsizing and standardizing of a power supply system reducing external component count and simplifying the circuit design.

### Typical Connection Diagram



Note 1:

The Pout (W) represents the thermal rating at Quasi-Resonant operation, and the peak power output is obtained by approximating 120 to 140 % of the above listed value. When the output voltage is low, and the ON-duty is narrow, the Pout (W) shall become lower than that of the above.

## Absolute Maximum Ratings

Absolute maximum ratings indicate sustained limits beyond which damage to the device may occur. All voltage parameters are absolute voltages referenced to terminals stated, all currents are defined positive into any lead. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions.

Symbol	Definition	Terminal	Max. Ratings	Units	Note
IDpeak	Drain Current * 1	1 - 3	11.2	A	Single Pulse
IDMAX	Maximum switching current *2	1 - 3	11.2	A	Ta=-20~+125
EAS	Single pulse avalanche energy *3	1 - 3	145	mJ	Single Pulse
					VDD=99V,L=20mH
					IL=3.6A
Vcc	Input voltage for control part	4 - 3	35	V	
VSSOLP	SS/OLP pin voltage	5 - 3	-0.5 ~ 6.0	V	
IFB	FB pin inflow current	6 - 3	10	mA	
VFB	FB pin voltage	6 - 3	-0.5 ~ 9.0	V	within the limits of IFB
VOCPBD	O.C.P/F.B pin voltage	7 - 3	-1.5 ~ 5.0	V	
PD1	Power dissipation of MOSFET *4	1 - 3	26.0	W	With infinite heatsink
			1.3		Without heatsink
PD2	Power dissipation for control part (MIC)	4 - 3	0.8	W	Specified by Vcc x Icc
TF	Internal frame temperature in operation	-	-20 ~ +115		Refer to recommended operating temperature
Top	Operating ambient temperature	-	-20 ~ +115		
Tstg	Storage temperature	-	-40 ~ +125		
Tch	Channel temperature	-	150		

\*1 Refer to MOS FET A.S.O. curve

\*2 Maximum switching current

The maximum switching current is the Drain current determined by the drive voltage of the IC and threshold voltage (Vth) of the MOS FET.

\*3 Refer to MOS FET Tch-EAS curve

\*4 Refer to MOS FET Ta-PD1 curve

**Electrical Characteristics (for Control IC)**

Electrical characteristics for control part (Ta=25 °C, Vin=20V, unless otherwise specified)

Symbol	Definition	Terminals	Ratings			Units	Note
			MIN	TYP	MAX		
<b>Power Supply Start-up Operation</b>							
V <sub>CC(ON)</sub>	Operation Start Voltage	4 - 3	16.3	18.2	19.9	V	V <sub>cc</sub> =0 19.9V
V <sub>CC(OFF)</sub>	Operation Stop Voltage	4 - 3	8.8	9.7	10.6	V	V <sub>cc</sub> =19.9 8.8 V
I <sub>CC(ON)</sub>	Circuit Current in Operation	4 - 3	-	-	6	mA	-
I <sub>CC(OFF)</sub>	Circuit Current in Non-Operation	4 - 3	-	-	100	μA	V <sub>cc</sub> =15V
f <sub>osc</sub>	Oscillation Frequency	1 - 3	19	22	25	kHz	-
V <sub>SSOLP(SS)</sub>	Soft Start Operation Stop Voltage	5 - 3	1.1	1.2	1.4	V	-
I <sub>SSOLP(SS)</sub>	Soft Start Operation Charging Current	5 - 3	-710	-550	-390	μA	-

<b>Normal Operation</b>							
V <sub>OCBPD(BS1)</sub>	Bottom-Skip Operation Threshold Voltage1	7 - 3	-0.72	-0.665	-0.605	V	-
V <sub>OCBPD(BS2)</sub>	Bottom-Skip Operation Threshold Voltage2	7 - 3	-0.485	-0.435	-0.385	V	-
V <sub>OCBPD(LIM)</sub>	Overcurrent Detection Threshold Voltage	7 - 3	-0.995	-0.94	-0.895	V	-
I <sub>OCBPD</sub>	OCP/BD Pin Outflow Current	7 - 3	-250	-100	-40	μA	-
V <sub>OCBPD(TH1)</sub>	Quasi-Resonant Operation Threshold Voltage 1	7 - 3	0.28	0.4	0.52	V	-
V <sub>OCBPD(TH2)</sub>	Quasi-Resonant Operation Threshold Voltage 2	7 - 3	0.67	0.8	0.93	V	-
V <sub>FB(OFF)</sub>	FB Pin Threshold Voltage	6 - 3	1.32	1.45	1.58	V	-
I <sub>FB(ON)</sub>	FB Pin Inflow Current (Normal Operation)	6 - 3	600	1000	1400	μA	-

# IRIS-W6753

## Electrical Characteristics (for Control IC), Contd.

Stand-by Operation							
$V_{CC(S)}$	Stand-by Operation Start Voltage	4 - 3	10.3	11.1	12.1	V	$V_{CC}=0 \rightarrow 12.2V$
$V_{CC(SK)}$	Stand-by Operation Start Voltage Interval	4 - 3	1.1	1.35	1.65	V	-
$I_{CC(S)}$	Stand-by Non-Operation Circuit Current	4 - 3	-	20	56	$\mu A$	$V_{CC}=10.2V$
$I_{FB(S)}$	FB Pin Inflow Current (Stand-by)	6 - 3	-	4	14	$\mu A$	$V_{CC}=10.2V$
$V_{FB(S)}$	Stand-by Operation FB Pin Threshold Voltage	6 - 3	0.55	1.1	1.5	V	$V_{CC}=12.2V$
$T_{ON(MIN)}$	Minimum ON Time	1 - 3	0.5	0.8	1.2	$\mu Sec$	-
Protection Operation							
$T_{ON(MAX)}$	Maximum ON Time	1 - 3	27.5	32.5	39	$\mu Sec$	-
$V_{SSOLP(OLP)}$	OLP Operation Threshold Voltage	5 - 3	4	4.9	5.8	V	-
$I_{SSOLP(OLP)}$	OLP Operation Charging Current	5 - 3	-16	-11	-6	$\mu A$	-
$V_{CC(OVP)}$	OVP Operation Voltage	4 - 3	25.5	27.7	29.9	V	$V_{CC}=0 \rightarrow 29.0V$
$I_{CC(H)}$	Latch Circuit Holding Current *5	4 - 3	--	45	140	$\mu A$	$V_{CC}=29.9 \rightarrow V_{CC(OFF)}-0.3V$
VCC(La.OFF)	Latch Circuit Release Voltage *5	4 - 3	6	7.2	8.5	V	$V_{CC}=29.9 \rightarrow 6V$

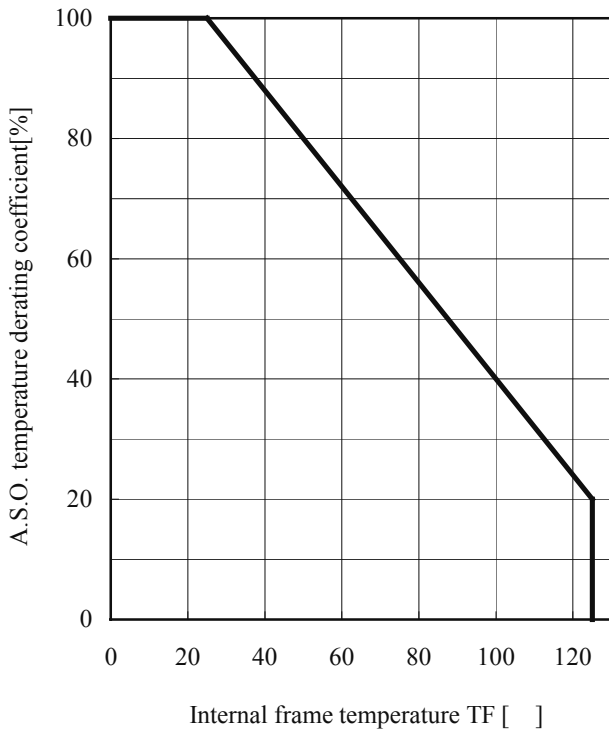
\*5 The latch circuit means a circuit operated O.V.P and O.L.P.

\*6 The current ratings are based on those of the IC , and plus(+) represents sink and minus(-) represents source.

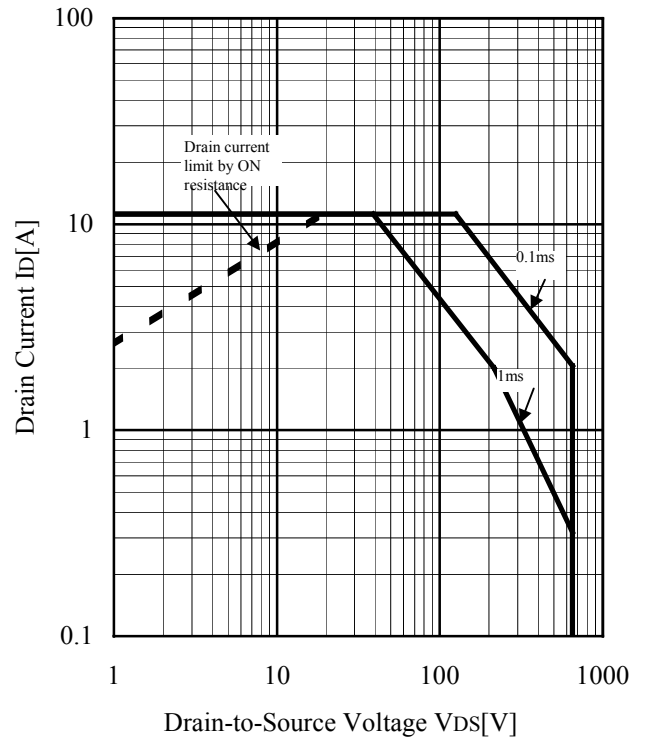
Electrical characteristics for MOSFET (Ta=25 deg C)

Symbol	Definition	Terminals	Ratings			Units	Note
			MIN	TYP	MAX		
V <sub>DSS</sub>	Drain-to-Source breakdown voltage	1 - 3	650	-	-	V	I <sub>D</sub> =300μA
I <sub>DSS</sub>	Drain leakage current	1 - 3	-	-	300	μA	V <sub>DS</sub> =650V
R <sub>DS(ON)</sub>	On-resistance	1 - 3	-	-	1.65		I <sub>D</sub> =1.4A
t <sub>f</sub>	Switching time	1 - 3	-	-	400	nSec	-
ch-F	Thermal resistance	-	-	-	2.0	/W	Between channel and internal frame

IRIS-W6753  
A.S.O. temperature derating coefficient curve

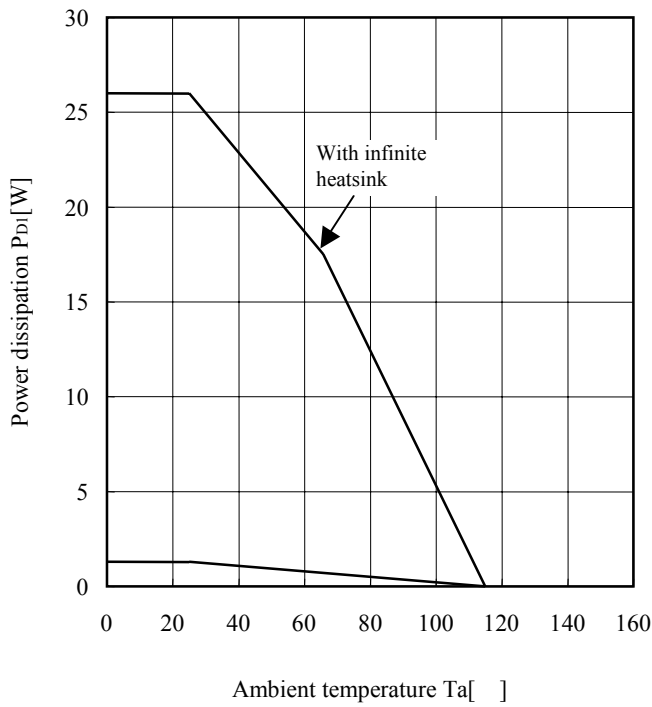


IRIS-W6753  
MOS FET A.S.O. curve

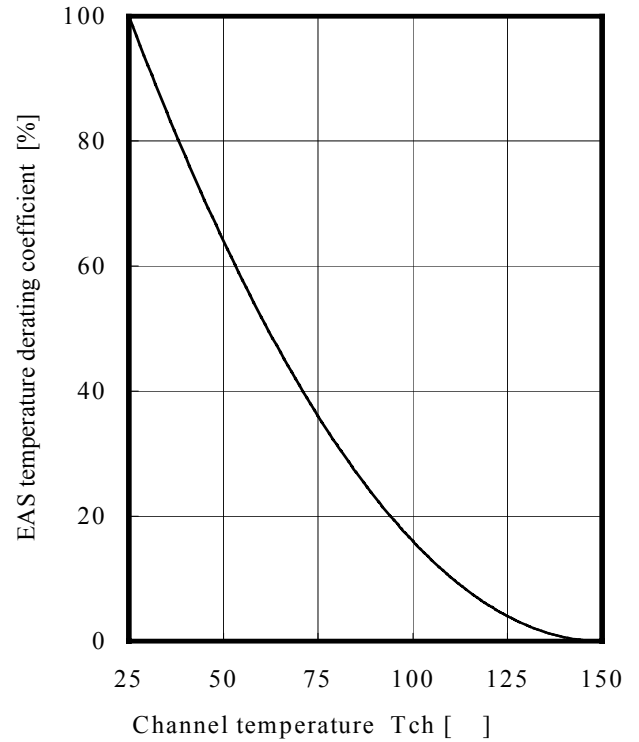


# IRIS-W6753

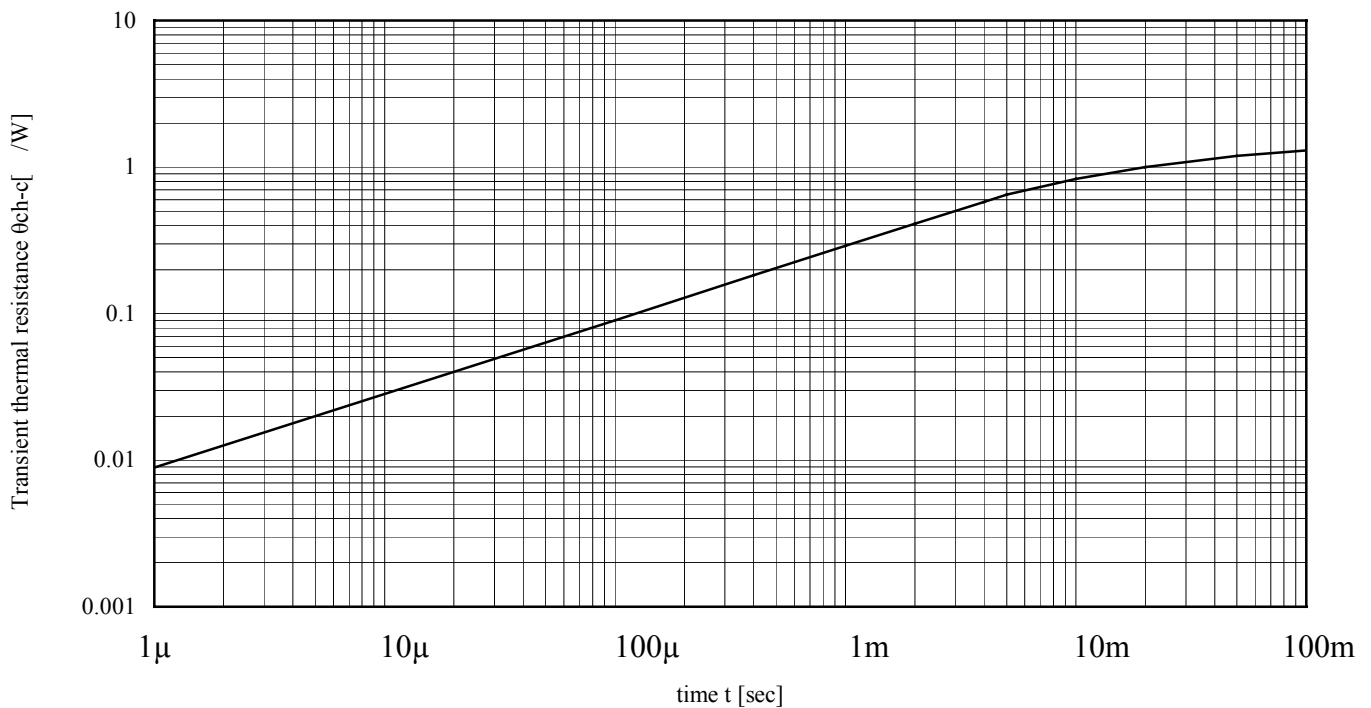
IRIS-W6753  
MOSFET Ta-PD1 Curve



IRIS-W6753  
Avalanche energy derating curve



STR-W6753  
Transient thermal resistance curve

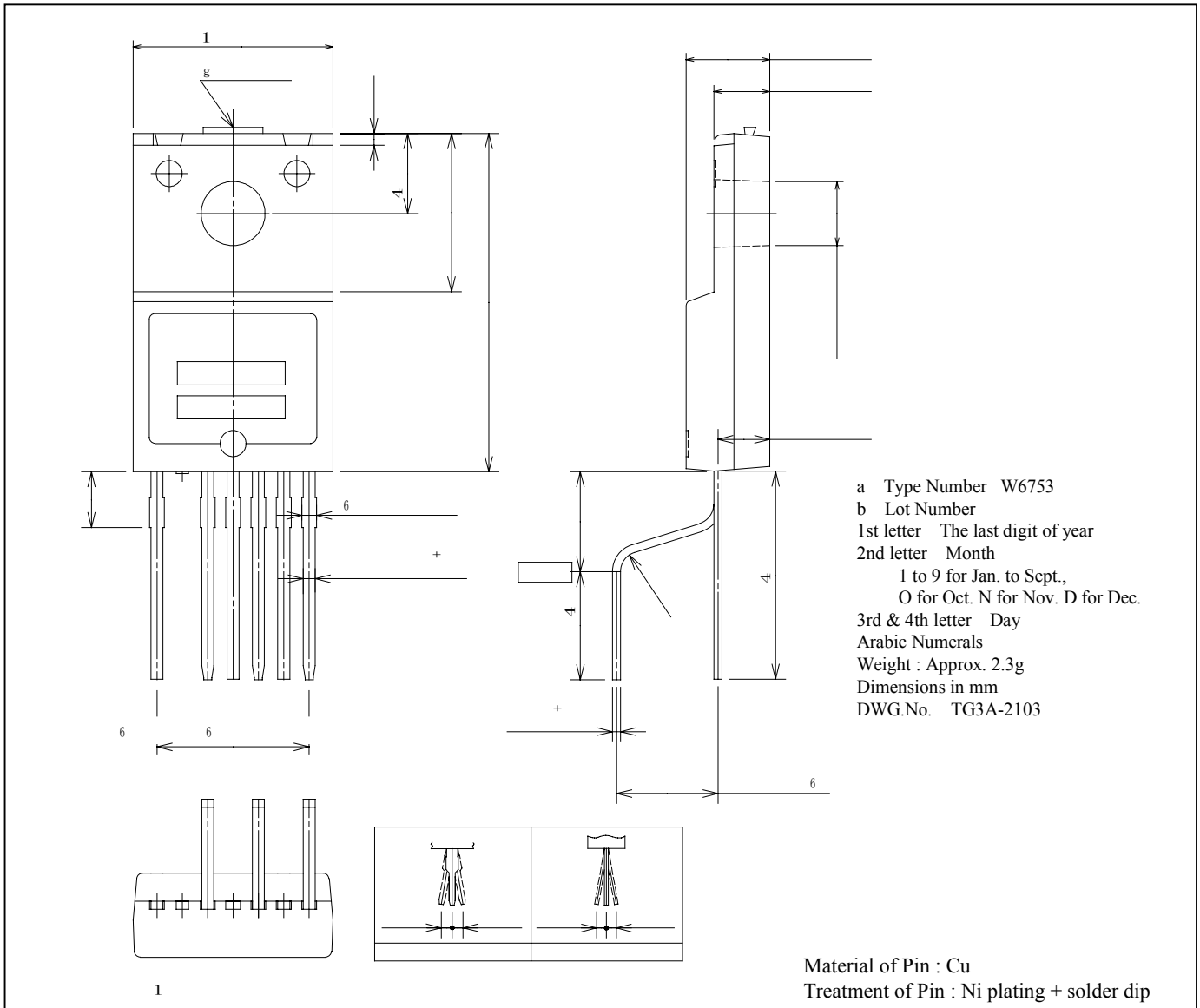




IRIS-W6753

Case Outline

International  
**IOR** Rectifier



Data and specifications subject to change without notice.

International  
**IOR** Rectifier

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